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Docket No. 8733.6836

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Duck-Kyun CHOI

GAU: 2823

SERIAL NO: 09/170,625

EXAMINER: S. Hawranek

FILING DATE: October 13, 1998

FOR: METHOD FOR FABRICATING A THIN FILM TRANSISTOR

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the Office Action dated December 8, 1999, Applicant requests that the application be amended as follows:

IN THE CLAIMS:

4. (Amended) The method of fabricating a thin film transistor according to claim 1, wherein the gate electrode is formed by at least one transition metal [material including] selected from the group consisting of Mo, Cr and Co.

Claim 5, line 2, please change "PH3" to - -PH₃- -.

7. (Amended) The method of fabricating a thin film transistor according to claim 6, wherein the metal layer is formed by at least one transition metal [material including] selected from the group consisting of Cu, Ni, Fe, Co, Ru, Rh, Pd, Os, Ir, Pt, Se, Ti, V, Cr, Mn, Zn, Au and Ag.

Claim 8, line 3, please change "the doped" to - -exposed- -.

10. (Amended) The method of fabricating a thin film transistor according to claim 9, wherein the electrodes are formed by a metal [material including] selected from the group

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